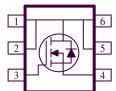
## **N-Channel Logic Level MOSFET**

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
$V_{DS}(V)$	$\mathbf{r}_{\mathrm{DS(on)}}\left(\Omega\right)$	$I_{D}(A)$			
30	$0.027 @ V_{GS} = 10 V$	6.3			
	$0.04 @ V_{GS} = 4.5V$	5.5			

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe TSOP-6 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	Maximum	Units		
Drain-Source Voltage			30	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$	Τ_	6.3			
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	ъ	5.2	A		
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	±20			
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	1.3	A		
D. D a	$T_A=25^{\circ}C$	D	1.6	$\mathbf{w}$		
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	rD	1.0	VV		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 5 sec	$R_{THJA}$	78.0	°C/W	

1

### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions	Limits			T I 24	
Parameter	Symbol	Symbol Test Conditions		Тур	Max	Unit	
Switch Off Characteristics							
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ	
Zero Gate Voltage Drain Current	<sup>1</sup> DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
Switch On Characteristics							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Durin Company A		$V_{GS} = 10 \text{ V}, I_D = 6.3 \text{ A}$			27	mΩ	
Drain-Source On-Resistance <sup>A</sup>	$r_{\mathrm{DS(on)}}$	$V_{GS} = 4.5 \text{ V}, I_D = 5.5 \text{ A}$			40		
Forward Tranconductance <sup>A</sup>	${f g}_{ m fs}$	$V_{DS} = 10 \text{ V}, I_D = 6.3 \text{ A}$		45		S	
On-State Drain Current <sup>A</sup>	I <sub>D(on)</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			A	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 1.3 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	V -15 V V -5 V I -62 A		9		nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 6.3 \text{ A}$ $R_{L} = 6 \Omega$		2.9			
Gate-Drain Charge	$Q_{\mathrm{gd}}$	$R_{\rm L} = 0.22$		3.2			
Switching Characteristics	<u> </u>	-					
Turn-On Delay Time	$t_{d(on)}$			6			
Rise Time	t <sub>r</sub>	$V_{DS} = 15 \text{ V}, R_L = 6 \Omega, I_D = 1 \text{ A},$		10		<b>n</b> c	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}$		18		ns	
Fall-Time	$t_{\mathrm{f}}$			5			

### Notes

- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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## Typical Electrical Characteristics (N-Channel)

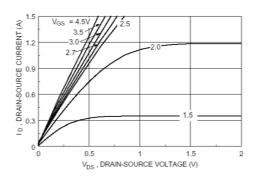


Figure 1. On-Region Characteristics

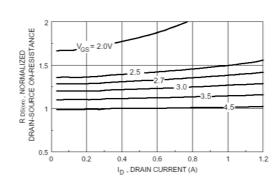


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

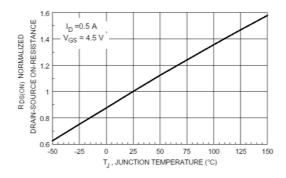


Figure 3. On-Resistance Variation with Temperature

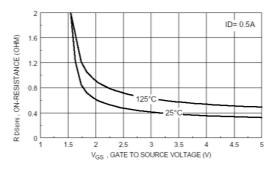


Figure 4. On-Resistance Variation with Gate to Source Voltage

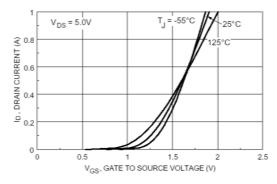


Figure 5. Transfer Characteristics

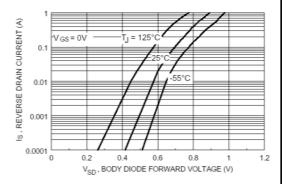


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

### Typical Electrical Characteristics (N-Channel)

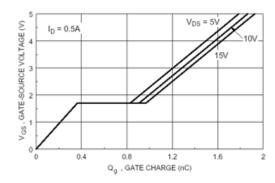


Figure 7. Gate Charge Characteristics.

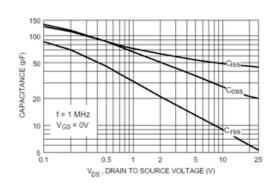


Figure 8. Capacitance Characteristics.

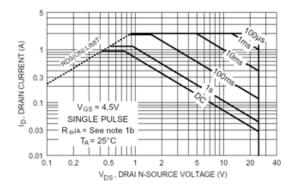


Figure 9. Maximum Safe Operating Area.

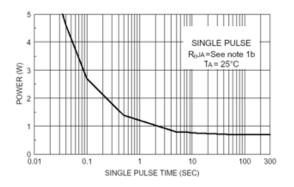


Figure 10. Single Pulse Maximum Power Dissipation.

#### **Normalized Thermal Transient Junction to Ambient**

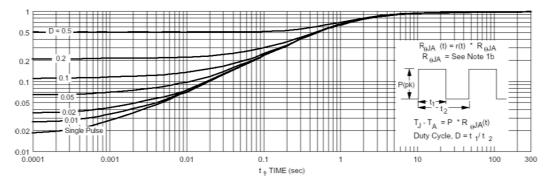
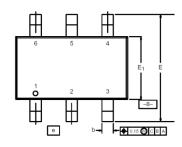
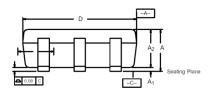


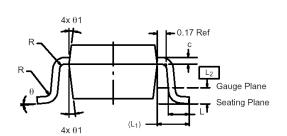
Figure 11. Transient Thermal Response Curve

# Package Information

TSOP-6: 6LEAD







	MIL	LIMET	ERS	RS INCHES		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.91	_	1.10	0.036	_	0.043
A <sub>1</sub>	0.01	_	0.10	0.0004	-	0.004
A <sub>2</sub>	0.84	_	1.00	0.033	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
С	0.10	0.15	0.20	0.004	0.006	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.106	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067
е	1.00 BSC			0.0394 BSC		
L	0.35	_	0.50	0.014	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	_	_	0.004	-	_
θ	0°	4°	8°	0°	4°	8°
$\theta_1$	7° Nom			7° Nom		